

isc N-Channel MOSFET Transistor

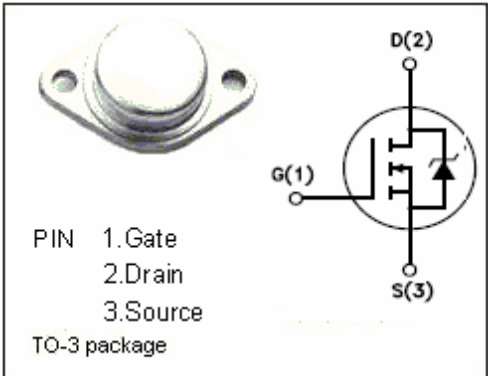
IRF256

DESCRIPTION

- Drain Current $I_D=20A@ T_C=25^{\circ}C$
- Drain Source Voltage
: $V_{DSS}= 275V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} =0.14 \Omega (\text{Max})$
- Nanosecond Switching Speed

APPLICATIONS

- Switching power supplies
- Switching converters,motor driver,relay driver

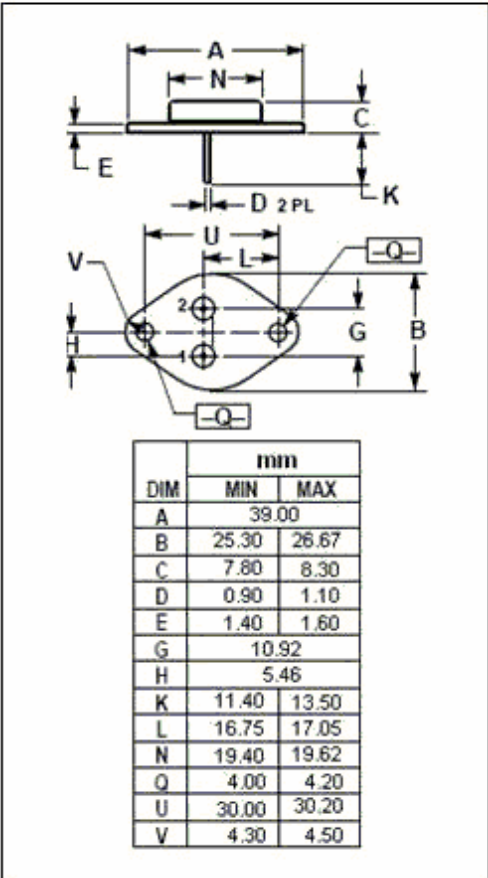


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	275	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^{\circ}C$	20	A
P_{tot}	Total Dissipation@ $T_C=25^{\circ}C$	150	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	0.83	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	30	$^{\circ}C/W$



isc N-Channel MOSFET Transistor**IRF256****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D =250μA	275			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =250μA	2.0		4.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =12A			0.14	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} =±20V; V _{DS} =0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =275V; V _{GS} =0			250	uA
V _{SD}	Diode Forward Voltage	I _S =20A; V _{GS} =0			1.8	V
C _{iss}	Input Capacitance	V _{DS} =25V; V _{GS} =0V; f _T =1MHz		2700		pF
C _{rss}	Reverse Transfer Capacitance			130		
C _{oss}	Output Capacitance			580		
t _r	Rise Time	I _D =16A; V _{DD} =95V; R _L =4.7 Ω		84	130	ns
t _{d(on)}	Turn-on Delay Time			19	29	
t _f	Fall Time			65	98	
t _{d(off)}	Turn-off Delay Time			75	110	